TOSHIBA Transistor Silicon NPN Epitaxial Type

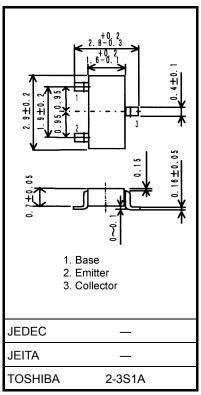
2SC5784

High-Speed Switching Applications DC-DC Converter Applications

- High DC current gain: $h_{FE} = 400$ to 1000 (IC = 0.15 A)
- Low collector-emitter saturation voltage: V_{CE} (sat) = 0.12 V (max)
- High-speed switching: $t_f = 45 \text{ ns} (typ.)$

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V _{CBO}	40	V	
Collector-emitter voltage		V _{CEX}	30	V	
Collector-emitter voltage		V _{CEO}	20	V	
Emitter-base voltage		V _{EBO}	7	V	
Collector current	DC	Ι _C	1.5	А	
	Pulse	I _{CP}	2.5	A	
Base current		Ι _Β	150	mA	
Collector power dissipation	t = 10 s	PC	750	mW	
	DC	(Note 1)	500		
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-55 to 150	°C	



Weight: 0.01 g (typ.)

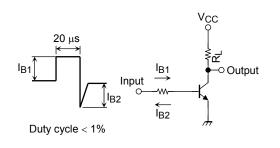
Note 1: Mounted on an FR4 board (glass epoxy, 1.6 mm thick, Cu area: 645 mm²)

Note 2: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

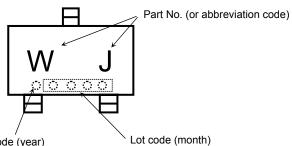
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current		I _{CBO}	$V_{CB}=40~V,~I_{E}=0$	_		100	nA
Emitter cut-off current		I _{EBO}	$V_{EB} = 7 V, I_{C} = 0$	_		100	nA
Collector-emitter breakdown voltage		V (BR) CEO	$I_{C} = 10 \text{ mA}, I_{B} = 0$	20		_	V
DC current gain		h _{FE} (1)	$V_{CE} = 2 V, I_C = 0.15 A$	400		1000	
		h _{FE} (2)	$V_{CE} = 2 V, I_C = 0.5 A$	200		_	
Collector-emitter saturation voltage		V _{CE (sat)}	$I_{C} = 0.5 \text{ A}, I_{B} = 10 \text{ mA}$	_		0.12	V
Base-emitter saturation voltage		V _{BE (sat)}	$I_{C} = 0.5 \text{ A}, I_{B} = 10 \text{ mA}$	_		1.10	V
Collector output capacitance		C _{ob}	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$	_	18		pF
Switching time	Rise time	tr	See Figure 1.	_	43		ns
	Storage time	t _{stg}	$V_{CC} \simeq 12 \text{ V}, \text{ R}_L = 24 \Omega$	_	295		
	Fall time	t _f	$I_{B1} = -I_{B2} = 17 \text{ mA}$	_	45		



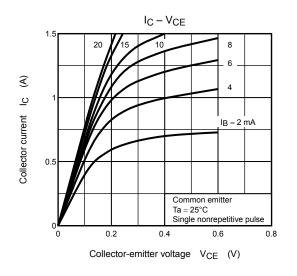
Marking

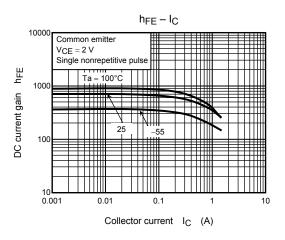


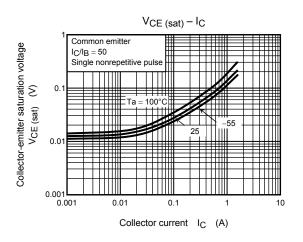
Lot code (year) Dot: even year No dot: odd year

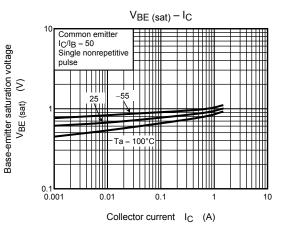
Switching Time Test Circuit & Timing Chart Figure 1

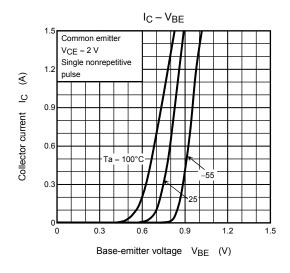
TOSHIBA

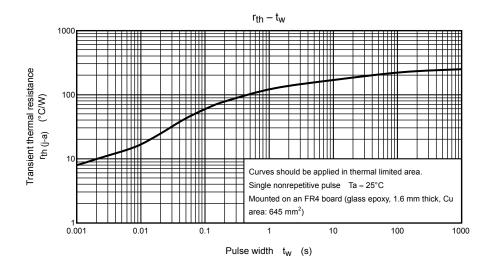












Safe Operating Area 10 IC max (pulsed) + 100 µs♦ 10 ms 1 ms♦ IC max (continuous)100 ms E Collector current IC 10 s DC operation (18 = 25°C)
 •: Single nonrepetitive pulse Ta = 25°C
 0.1
 0.1 Note that the curves for 100 ms*, 10 s* and DC operation* will be different when the devices aren't mounted on an FR4 board (glass epoxy, 1,6 mm thick, Cu area: 645 mm²). These characteristic curves must be derated linearly with increase in temperature.
 0.1 (Ta = 25°C) - x ------VCEO r 10 100 Collector-emitter voltage V_{CE} (V)

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20070701-EN

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